



GMM

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MIKROELEKTRONIK,
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Program and Invitation

ICPT

International
Conference on
Planarization/CMP Technology

October 25 – 27, 2007

Hilton Hotel, Dresden, Germany

www.icpt2007.com

in cooperation with:

German CMP User Group

Japanese Planarization and CMP Technical Committee (JSPE)

Korea CMP User Group (KCMPUG)

Northern California Chapter AVS (NCCAVS) CMPUG

Taiwan CMP User Group (CMPUGTW)


Fraunhofer Institut
Siliziumtechnologie



VDE

IPR2024-00534
Samsung Electronics Co. Ltd. et al v. Chien-Min Sung
Samsung's Exhibit 1022
Ex. 1022, Page 1

Conference Objective

Over the last 15 years, Chemical Mechanical Polishing (CMP) has developed into one of the key technologies in the ULSI fabrication process. It can be viewed as an enabling technology for manufacturing state-of-the-art microprocessors, high-density memories and other advanced microelectronic circuits. Without CMP, accurate printing of nanometer chip structures is impossible. CMP has helped to introduce multilevel interconnection and the employment of copper metallization. Emerging CMP applications include MEMS and nanotechnology, but advancements in CMP also stimulate related areas like wafer polishing and production of optical surfaces. In order to keep pace with future ULSI developments, improved Chemical Mechanical Polishing processes have to be available for FEOL and BEOL applications. For reasons of productivity enhancement, tool reliability improvements, cost reductions, process automation and advanced process control are required. Finally, new fields of applications for CMP, which certainly exist plentiful, have to be discovered and developed.

Upon several requests towards increased co-operation of the local CMP users groups from Germany, Japan, Korea, Taiwan, and the United States of America, the idea of a joint international CMP conference emerged in 2005. Following successful conferences in Tokyo, Japan (PacRim-CMP 2004), Seoul, Korea (PacRim-CMP 2005) and Foster City, California, USA (ICPT 2006), the International Conference on Planarization/CMP Technology ICPT 2007 in Dresden, Germany, is organized by the German CMP User Group within the German VDE/VDI-Society Microelectronics, Micro- and Precision Engineering. The mission of this conference is the provision of a forum for the worldwide CMP community for exchange and discussion on a high scientific level in order to support and advance the developments of this highly important field of semiconductor manufacturing.

Dr. Gerfried Zwicker
Fraunhofer Institute for Silicon Technology (ISIT)
Conference Chairman

List of Contents

	Page
Organizing Committee	4
Organizer	5
Program Overview	6
Thursday, October 25, 2007	6
Poster Session 1	10
Friday, October 26, 2007	14
Poster Session 2	18
Saturday, October 27, 2007	22
Conference Information	23
Conference Hours	23
Registration Hours	23
Exhibition	23
Information for Authors	23
General Information	24
ICPT Secretariat	24
Conference Fees	24
Conference Registration	24
Online Registration	25
Payment	25
Cancellation	25
Proceedings	25
Venue	26
Hotel Reservation	26/27
Busshuttle to the Conference Hotel	27
Insurance	27
Passport and Visa Requirements	28
Transport	28
List of Exhibitors	29
List of Sponsors	32

Organizing Committee

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Institute for Silicon Technology, Germany

Organizer

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PROGRAM OVERVIEW

Wednesday, October 24, 2007

17:00 h Registration

- 19:00 h

19:00 h Set up for Technical exhibition

Thursday, October 25, 2007

07:30 Registration

09:00 Welcome to Conference

G. Zwicker, Fraunhofer Institute for Silicon Technology, Itzehoe, Germany

09:05 Challenges and opportunities of semiconductor manufacturing between research and volume production

H. Deppe, AMD Dresden, Germany

Session 1: CMP Fundamentals 1

Session Chairs:

S.V. Babu, Clarkson University;

Peter Thieme, Qimonda

09:30 CMP Modeling as a Part of Design for Manufacturing (Invited)

S. Tripathi, A. Monvoisin, D. Dornfeld, F.M. Doyle;

University of California at Berkeley, CA, USA

09:55 Pad Surface Analysis and Conditioning Effects: Implications on Process Design, Break-in Response and Next Generation Pad and Conditioning Platforms

S. Lawing, C. Juras;

Rohm and Haas Electronic Materials, Phoenix, AZ, USA

- 10:15 Tribological, Kinetic, Thermal and Flow Characteristics of Retaining Rings in STI CMP**
X. Wie¹, A. Philipossian^{1,2}, Y. Zhuang^{1,2},
Y. Sampurno¹, F. Sudargho^{1,2}, C. Wargo³,
L. Borucki²;
¹University of Arizona, Tucson, AZ, USA;
²Araca Inc, Tucson, AZ, USA;
³Entegris Corp., Billerica, MA, USA
- 10:35 In-Situ Investigation of Wafer-Slurry-Pad Interactions during CMP**
C. Gray¹, A. Mueller¹, J. Vlahakis¹, V.P. Manno¹,
C. Rogers¹, R. White¹, S. Anjur², M. Moinpour³,
¹Tufts University, Medford, MA, USA;
²Cabot Microelectronics Corp., Aurora, IL, USA;
³Intel Corp., Santa Clara, CA, USA
- 10:55 Coffee Break**
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)

Session 2: Metal CMP 1

Session Chairs:
Yohei Yamada, Hitachi;
Karl Hensen, BASF

- 11:55 CMP of a Ru Based Layer in an Advanced Cu Low-k Stack (Invited)**
J. Vaes¹, F. Sinapi¹, J. L. Hernande¹,
G. Santoro², O. Nguyen², J. Wang³;
¹IMEC, Heverlee, Belgium;
²Applied Materials, Heverlee, Belgium;
³Applied Materials, Sunnyvale, CA, USA
- 12:20 Integrated Profile Control from ECP to CMP**
U. Stöckgen, S. Wehner, A. Preuß, J. Heinrich,
J. Groschopf; AMD Fab36, Dresden, Germany
- 12:40 A Systematic Study on the Impact of Polymer Additives in Bulk Copper Slurry on Copper CMP**
H. Chou, W.L. Kim, J.I. Noh, I. Lee;
Samsung Cheil Industries, Korea

- 13:00 Full Sequence eCMP for Advanced Low Stress Copper Planarization**
J. Groschopf¹, K. Steffen¹, R. Donohue², P. Lo-Menzo², R. Seidel¹, M. Grillberger¹, H. Gu³, Y. Hu³, Y. Wang³, W.-Y. Hsu³;
¹AMD Fab36, Dresden, Germany;
²Applied Materials, Dresden, Germany;
³Applied Materials, Sunnyvale, CA, USA
- 13:20 Lunch / Coffee**
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)

Session 3: Wafers and New Materials

Session Chairs:

Haedo Jeong, Pusan National University;

Knut Gottfried, Fraunhofer IZM Chemnitz

- 14:50 Challenges in CMP of New Materials from Carbon Nanotubes to Moisture Sensitive Surfaces (Invited)**
Y. Li, Clarkson University; Potsdam, NY, USA
- 15:15 Influence of the Wafer Shape on Polishing Performance for 300 mm Prime Wafer Polishing**
M. Langenkamp, J. Kanzow, G. Mörsch; Peter Wolters AG, Rendsburg, Germany
- 15:35 Application of CMP to the Cladding Layer of MRAM**
S.-H. Wang, D.-Y. Shu, K.-C. Lin, C.-T. Yen, M.-J. Tsai; Industrial Technology Research Institute, Hsinchu, Taiwan
- 15:55 TaN Formation by CMP for Cross-Spacer Phase Change Memory**
K.-C. Lin, C.-W. Chen, S.-H. Wang, D.-Y. Shu, M.-J. Tsai, M.-J. Kao; Industrial Technology Research Institute, Hsinchu, Taiwan
- 16:15 Coffee Break**
Poster Session 1: CMP of Poly-Si, Dielectrics and Metals, Fundamentals
(all Posters in Poster Session 1 are listed on page 10)

Session 4: Poly-Si & Dielectric CMP 1

Session Chairs:

Mansour Moinpour, Intel;

Dorit Wecker, Infineon Technologies

- 17:15 Planarization of the Poly-Si Gate for Non Volatile Memories (Invited)**
*L. Baud¹, L. Canevari², C. Romanelli²,
G. Spinolo², M. Rivoire³;
¹CEA-LETI, Grenoble, France;
²ST Microelectronics, Agrate Brianza, Italy;
³ST Microelectronics, Crolles, France*
- 17:40 Effect of Polish Stopper Film in STI-CMP for 45nm Node Devices and Beyond**
*T. Watanabe¹, S. Shibata², N. Idani¹, M. Kase¹,
M. Miyajima¹;
¹Fujitsu Ltd., Tokyo, Japan;
²Fujitsu Laboratories Ltd., Tokyo, Japan*
- 18:00 Influence of STI Trench Fill and Dummy Design on CMP Behavior**
*P. Ong¹, K. Devriendt¹, A. Redolfi¹, Y. Okuno²,
J.L. Hernandez¹,
¹IMEC, Leuven, Belgium;
²Matsushita, Japan*
- 18:20 Defectivity Improvement for Fixed Abrasive Based STI CMP in Advanced Logic Technology**
*B. Reinhold¹, J. J. Gagliardi², S. Endle²,
¹AMD Fab36, Dresden, Germany;
²3M Electronics Markets Materials Division,
St. Paul, MN, USA*
- 18:40 End of Sessions (Day 1)**
- 19:30 Conference Dinner**
at the Pulverturm
An der Frauenkirche 12, 01067 Dresden

Thursday, October 25, 2007
Poster Session 1: CMP of Poly-Si,
Dielectrics and Metals, Fundamentals

In situ Studies of Copper CMP with Arginine and Peroxide Based Slurries

Y. Nagendra Prasad, S. Ramanathan; Indian Institute of Technology-Madras, Chennai, India

Bench Top Dual Mode eCMP Polisher with Multi Sensing Metrology

N. Gitis, V. Khosla, M. Vinogradov; CETR, Campbell, CA, USA

Charakterization of Residual Stress Change of Dielectrics in W-CMP Process Using Finite Element Method Analysis

*A. Fukuda¹, Y. Mochizuki¹, H. Hiyama¹, M. Tsujimura²,
¹Ebara Research Co., Ltd., Kanagawa, Japan;
²Ebara Corp., Kanagawa, Japan*

The Study of CVD Diamond Conditioner

N. Rikita, R. Matsuki, H. Kobayashi, M. Nakamura, K. Chida; Mitsubishi Materials Corp., Saitama, Japan

Voltage-Activated Electrochemical Reactions of Copper for Electrochemical Mechanical Polishing Applications

*Y.-J. Seo¹, S.-I. Lee¹, S.-W. Park², S.-J. Han², Y.-K. Lee², W.-S. Lee²;
¹Daebul University, South Korea;
²Chosun University, South Korea*

Effect of Pad Hole on ECMP Process

*S. Jeong¹, H. Lee¹, J. Park¹, H. Jeong¹, H. Kim²;
¹Pusan National University, Busan, Korea;
²Korea Institute of Industrial Technology, Busan, Korea*

Next Generation Barrier CMP Technology for 45nm and Beyond

C. Ye, H. Li; Rohm and Haas Electronic Materials CMP Technology, Newark, DE, USA

Poly-CMP Integration for Sub 90 nm Self-aligned Floating Gate Flash Memories

M. Mariani, C. Romanelli, L. Canevari; ST Microelectronics, Agrate Brianza, Italy

Pre-polishing Transient Effects Investigation for Chemical Mechanical Planarization Processes

A. Filippini¹, C. Patini²;

¹*ST Microelectronics, Agrate Brianza, Italy;*

²*Applied Materials, Caponago, Italy*

Effect of Ceria Size and Concentration in Shallow Trench Isolation (STI) Chemical Mechanical Polishing (CMP)

S. Pandija¹, G. Crinière², C. Ceintrey², S.V. Babu¹;

¹*Clarkson University, Potsdam, NY, USA;*

²*Rhodia Electronics and Catalysis, France*

Next Generation Chemical Mechanical Planarization Slurries for Polishing Silicon on Advanced Devices

M. L. White, C. W. Nam, F. Batllo, A. Walters; Cabot Microelectronics Corp., Aurora, IL, USA

Control of Flatness for Chemical Mechanical Planarization

A. Nutsch, L. Pfitzner; Fraunhofer Institute for Integrated Systems and Device Technology, Erlangen, Germany

A Study on Delamination of Low-k Dielectrics During Cu-low k CMP

J.-H. Han¹, D.-H. Chung¹, B.-R. Park¹, J.-B. Yim¹,

T.-H. Ahn¹, J.-G. Park²;

¹*Samsung Electronics Ltd., Kyunggi-Do, Korea;*

²*Hanyang University, Ansan, Korea*

Effect of Slurry pH on Poly Silicon CMP

Y.-J. Kang¹, B.-K. Kang¹, J.-G. Park¹, Y.-K. Hong²,

S.-Y. Han², S.-K. Yun², B.-U. Yoon², C.-K. Hong²,

¹*Hanyang University, Ansan, Korea;*

²*Samsung Electronics, Hwasung, Korea*

Development of Post Ru CMP Cleaning Solutions

I.-K. Kim, B.-G. Cho, T.-G. Kim, J.-G. Park; Hanyang University, Ansan, Korea

Pad Roughness Effects on Removal Rate and Selectivity in a STI Ceria CMP Process

F. C. Meyer¹, C.-H. Kuo², C. Rudolph¹, P. Faustmann¹;

¹Qimonda, Dresden, Germany;

²Nanya Technology Corp., Taoyuan, Taiwan

CMP Issues Arising from Novel Materials and Concepts in the BEOL of Advanced Microelectronic Devices

K. Gottfried¹, I. Schubert¹, K. Schulze², S. Schulz²,

T. Gessner^{1,2}; ¹Fraunhofer-Institute Reliability and Micro-Integration, Chemnitz, Germany;

²Technical University Chemnitz, Germany

Impact of Ceria Properties and CMP Parameters on STI CMP Performance

J. De Messemaeker¹, F. Sinapi², P. Ong², S. Put¹,

D. Nelis¹, J. van den Bosch¹, Y. Strauven¹, P. Lippens¹, K. Devriendt²;

¹Umicore R&D, Olen, Belgium;

²IMEC, Leuven, Belgium

Major Influences of Shaping and Profiling of Cu ECP and CMP on Feature Level for Process Stabilizing

G. Marxsen, M. Nopper, T. Ortleb, M. Lehr, T. Merbeth, T. Roessler; AMD, Dresden, Germany

Advanced W-CMP Slurry for High Planarity

R. Tanaka, H. Nojo, K. Yoshida, A. Isobe; Nitta Haas Inc., Kyotanabe-Shi, Japan

New Polish Chemistry and Process for Improved Fixed Abrasive CMP Performance

G. Menk, R. Marks, G. Leung, A. Iyer, J. Diao, Y. Zhou, C. Lee; Applied Materials, Sunnyvale, Ca, USA

Improvement of Uniformity Post Oxide CMP by Optimization of Pre Processes

T. Schest, J. Plagmann, S. Willkofer; Infineon Technologies, Regensburg, Germany

**Novel Chemicals and Mechanisms that Control Dishing
and Overpolish Window Independent of Corrosion
Inhibitor Effects**

*S. Shrauti, B. Palmer, A. Meyers, G. Zhang, A. Zutshi;
DuPont Air Products NanoMaterials, Tempe, AZ, USA*

**Application of the Copper Damascene Process for the
Preparation of Electromigration Test Structures**

*M. Stangl¹, V. Hoffmann¹, K. Wetzig¹, U. Künzelmann²,
J.-W. Bartha²;*

¹*Leibniz-Institute for Solid State and Materials Research
(IFW) Dresden;*

²*Dresden University of Technology, Dresden, Germany*

Friday, October 26, 2007

08:30 Morning Welcome

G. Zwicker, Fraunhofer Institute for Silicon Technology, Itzehoe, Germany

Session 5: Poly-Si & Dielectric CMP 2

Session Chairs:

Jin-Goo Park, Hanyang University;

Georg Moersch, Peter Wolters AG

08:35 Materials & Metrology Challenges in Planarization and Interconnect Technologies (Invited)

M. Moinpour, Intel, Santa Clara, CA, USA

09:00 Integrative Defect Reduction at STI CMP (Invited)

R. Becker, W. Tittes, A. Boenicke, S. Peters, M. Probst, D. Schulze, S. Cwikla, S. Loesch; Infineon Technologies, Dresden, Germany

09:25 Novel Slurries for Achieving a Low Silicon Dioxide and High Silicon Nitride Removal During Chemical-Mechanical Planarization

A. Natarajan, Dandu Veera P.R., S.V. Babu; Clarkson University, Potsdam, NY, USA

09:45 Applications of Shear Force Spectral Analysis in STI CMP

*Y. Sampurno¹, F. Sudargho^{1,2}, Y. Zhuang^{1,2}, T. Ashizawa³, H. Morishima³, A. Philipossian^{1,2};
¹University of Arizona, Tucson, AZ, USA;
²Araca Inc., Tucson, AZ, USA;
³Hitachi Chemical Co., Tokyo, Japan*

10:05 Study of STI CMP Process Control on High Aspect Ratio Gap-fill Topographies by Motor Current EPD

*C.-H. Kuo¹, F. C. Meyer², M. Hollatz², P. Faustmann², K.-W. Chung¹, C.-K. Lin¹;
¹Nanya Technology Corp., Taoyuan, Taiwan;
²Qimonda, Dresden, Germany*

10:25 Coffee Break
Poster Session 2: Defects and Metrology, New Materials, Slurry, Pad Conditioning
(all Posters in Poster Session 2 are listed on page 18)

Session 6: Metal CMP 2

Session Chairs:
Halbert Tam, JSR Micro;
Uwe Stöckgen, AMD

- 11:25 Copper Oxidization Formation Analysis for Improving TDDDB Reliability (Invited)**
Y. Yamada¹, Y. Yagi², N. Konishi¹, N. Ogiso²,
K. Katsuyama¹, S. Asaka¹, J. Noguchi¹,
T. Miyazaki²;
¹Hitachi Ltd., Tokyo, Japan;
²Sanyo Chemical Industries Ltd., Kyoto, Japan
- 11:50 Influence of Low-k Films on Barrier Removal Rate Variation Between Blanket and Patterned Wafers**
Y. Li¹, C. Burkhard¹, C. Wang¹, R. Wen²,
D. Mahulikaar²;
¹Clarkson University, Potsdam, NY, USA;
²Planar Solutions, Mesa, AZ, USA
- 12:10 Evaluation of Cu CMP Barrier Slurries for Ultra Low-k Dielectric Film (k~2.4) for 45nm Technology**
F. Zhao¹, L. Economikos³, W.-T. Tseng²,
H.-K. Kim³, Edward Engbrecht², Jing Hui Li¹,
Wu Ping Liu¹, M. Chae⁴, L. M. Nicholson⁴;
¹Chartered Semiconductor Manufacturing Ltd.;
²IBM Systems and Technology Group;
³Samsung Electronics Co., Ltd.;
⁴Infineon Technologies AG
- 12:30 Evaluation and De-coupling of Electrochemical and Mechanical Effects of Diluted WCMP Commercial Slurry on Tungsten Removal Rate**
D. M. Gianni^{1,2}, A. Mazzarolo³, N. Masciocchi²,
A. Maspero², G. Spinolo¹, A. Vicenzo³;
¹STMicroelectronics, Agrate Brianza, Italy;
²Universita dell' Insubria, Como, Italy;
³Polytecnico di Milano, Milan, Italy

12:50 Lunch / Coffee
**Poster Session 2: Defects and Metrology,
New Materials, Slurry, Pad Conditioning**
*(all Posters in Poster Session 2 are listed on
page 18)*

Session 7: Defects and Metrology

Session Chairs:

*Keiichi Kimura, Kyushu Institute of
Technology;*

*Johann Wolfgang Bartha, Dresden
Technical University*

**14:20 Post-CMP Cleaning: Interaction between
Particles and Surfaces (Invited)**
J.-G. Park; Hanyang University, Ansan, Korea

**14:45 Wafer Edge / Bevel Treatment of Device
Wafers by Means of CMP**
*A. Wieters, P. Thieme; Qimonda, Dresden,
Germany*

**15:05 Impacts on Microscratching in CMP
Processes in High Volume Production**
*G. Marxsen, S. Lingel, J. Schlott, A. Hoefgen;
AMD, Dresden, Germany*

**15:25 Oxide Thickness Profile Measurement by
Dispersive White-Light Interferometry
(Invited)**
*H. Jeong¹, B. Park¹, Y. Kim¹, H. Kim², Y. Ghim³,
J. You³, S. Kim³;*
¹Pusan National University, Busan, Korea;
*²Korea Institute of Industrial Technology, Busan,
Korea;*
*³Korea Advanced Institute of Science and
Technology, Daejeon, Korea*

15:50 Coffee Break
**Poster Session 2: Defects and Metrology,
New Materials, Slurry, Pad Conditioning**
*(all Posters in Poster Session 2 are listed on
page 18)*

Session 8: CMP Fundamentals 2

Session Chairs:

Ara Philipossian, University of Arizona;

Katrin Blum, IHP Frankfurt/Oder

- 16:45 Full-Chip CMP Simulation System (Invited)**
*D. Fukuda¹, T. Shibuya¹, N. Idani²,
T. Karasawa²;*
¹*Fujitsu Laboratories Ltd., Kawasaki, Japan;*
²*Fujitsu Ltd, Kawasaki, Japan*
- 17:10 Greenwood-Williamsson Model for Pattern-Dependent Planarization**
R. Rzehak, B. Vasilev; Qimonda, Dresden, Germany
- 17:30 Study on Material Removal Phenomena in CMP Process**
*K. Kimura¹, Y. Hashiyama¹,
P. Khajornrungruang¹, H. Hiyama²,
Y. Mochizuki²;*
¹*Kyushu Institute of Technology, Fukuoka, Japan;*
²*Ebara Research, Kanagawa, Japan*
- 17:50 Modeling and Optimal Control of Chemical Mechanical Planarization**
*S. Dürigen^{1,2}, P. Benner¹, U. Stöckgen²,
J. Heinrich²;*
¹*Technical University Chemnitz, Germany;*
²*AMD Fab36, Dresden, Germany*
- 18:10 End of Sessions (Day 2)**

Friday, October 26, 2007
Poster Session 2
Defects and Metrology, New Materials,
Slurry, Pad Conditioning

**Development of Planarity Improved Abrasive-Free
Copper CMP Slurry and Practical Non-Selective Barrier
CMP Slurry Based on Electrochemical Study**

*J. Amanokura¹, K. Mabuchi², T. Sakurada¹, Y. Nomura¹,
M. Habiro¹, H. Akahoshi²;*

¹Hitachi Chemical Co., Ltd., Hitachi, Japan;

²Hitachi Ltd., Hitachi, Japan

**The Organic Diamond Disk (ODD) for Dressing
Polishing Pads of Chemical Mechanical Planarization**

J. C. Sung¹, C.-S. Chou¹, M. Sung²;

¹KINIK Company, Taipei, Taiwan;

²Advanced Diamond Solutions, San Francisco, CA, USA

**Modeling for Pad Wear Control During Conditioning in
CMP**

*T. Kasai, S. Anjur, H. Siriwardane, P. Feeney; Cabot
Microelectronics Corp., Aurora, IL, USA*

**The Fabrication of Ideal Diamond Disk (IDD) by Casting
Diamond Film on Silicon wafer**

*J. C. Sung¹, Y.-T. Chen², M.-C. Kan¹, H.-K. Chang¹,
M. Sung³;*

¹KINIK Company, Taipei, Taiwan;

²National Defense University, Taoyuan, Taiwan;

*³Advanced Diamond Solutions Inc., San Francisco, CA,
USA*

**Three-Dimensional Metrology for CMP Process
Evaluation with In-line Wide-Area Atomic Force
Microscope**

*K. Murayama, T. Morimoro, Y. Kunitomo, M. Edamura,
S. Sekino, T. Kurenuma; Hitachi-kenki Fine Tech Co., Ltd.,
Ibaraki, Japan*

**Pad Surface Microstructure and Optimization of the
Conditioning Sweep**

*L. Borucki¹, X. Wei², Y. Zhuang^{1,2}, A. Philipossian^{1,2},
D. Slutz³;*

¹Araca Inc., Tuscon, AZ, USA;

²University of Arizona, Tucson, AZ, USA;

³Morgan Advanced Ceramics, Allentown, PA, USA

Improvements of Electrical and Optical Property of Organic Light Emitting Diode Using Chemical Mechanical Polishing Process

G.-W. Choi¹, W.-S. Lee¹, Y.-J. Seo²;

¹Chosun University, South Korea;

²Daebul University, South Korea

Development of AE Monitoring System for CMP Process

S. Park¹, S. Joo¹, Y. Kim¹, H. Jeong¹, H. Kim²;

¹Pusan National University, Busan, Korea;

²Korea Institute of Industrial Technology, Busan, Korea

Reduction of Dishing in Polysilicon CMP for MEMS Application by Using Protective Layer and High Selectivity

W. Shin¹, S. Park², H. Kim³, K. Park¹, H. Cho¹, S. Joo¹, H. Jeong¹;

¹Pusan National University, Busan, Korea;

²University of California, Berkeley, CA, USA;

³Korea Institute of Industrial Technology, Busan, Korea

Experimental Analysis on CMP Mechanism of Single Crystal SiC

H. Lee¹, S. Jeong¹, H. Seo¹, B. Park¹, J. Oh¹, H. Jeong¹, H. Kim²;

¹Pusan National University, Busan, Korea;

²Korea Institute of Industrial Technology, Busan, Korea

Optimized and Customized CMP Conditioner Design for Next Generation Oxide/Metal CMP

T. Hwang, R. Vedantham, T. Puthanangady; Saint-Gobain High Performance Materials, Northboro, MA, USA

Impact in the Conditioning and Cleaning of Unwoven Fabric Polyester Pads with a High Pressure Micro Jet (HPMJ) on Silicon Polishing

K. Miyachi¹, Y. Seike¹, S. Haba², S. Kurokawa³, T. K. Doi³;

¹Asahi Sunac Corp., Aichi, Japan;

²Nitta Haas Inc., Tokyo, Japan;

³Kyushu University, Fukuoka, Japan

Large Particle Counting for Quality Control of CMP Slurries

A. Nogowski¹, M. Stintz¹, H. Barthel²;

¹Technical University Dresden, Germany;

²Wacker-Chemie AG, Burghausen, Germany

Prime Wafer Geometry Improvement During Haze-free Polishing with Peter Wolters Polishing Head “M-Carrier”

J. Kanzow, M. Langenkamp, G. Mörsch; Peter Wolters AG, Rendsburg, Germany

Damascene Metal Gate Technology: A Front-end CMP Based Universal Platform for High-k Evaluation at the Device Level

R. Endres, U. Schwalke; Technical University Darmstadt, Germany

Defectivity Reduction in a Poly-Si CMP for SAFG Definition (in NOR Application)

L. Canevari, C. Romanelli, G. Spinolo, V. Bontempo; ST Microelectronics, Agrate Brianza, Italy

Development of Copper Post-CMP Cleaning Chemistries Compatible with Advanced Barrier Materials

D. Tamboli, M. Rao, G. Banerjee; Air Products and Chemicals, Allentown, PA, USA

Post-CMP Clean PVA Brush Design Advancements and Characterization in Cu/Low-k Applications

R. K. Singh, C. R. Wargo, D. W. Stockbower; Entegris Inc., Billerica, MA, USA

Laser Scattering Technique for Characterizing Defects and Surface Morphology in the Fixed Abrasive CMP Process

J. Gagliardi¹, E. Olson¹, U. Mahajan², H. Zhang², C. Douglas²;

¹3M Corporation, St. Paul, MN, USA;

²KLA-Tencor Corporation, Milpitas, CA, USA

Enhanced Control and Manufacturing for CMP Processing with Advanced Blending and Delivery of Slurries

G. Liu, R. Moulton, L. Han, G. Flores; ChemFlow Systems Inc., San Jose, CA, USA

Conditioning of CMP Pad to Reinstate Pad Surface Function

K. Kadomura¹, T. Fukunishi², Y. Umezaki³, S. Kurokawa³, T. Doi³;

¹A.L.M.T. Diamond Corp., Hyogo, Japan;

²A.L.M.T. Corp., Hyogo, Japan;

³Kyushu University, Fukuoka, Japan

Effect of Diamonds on Pad Recovery in Oxide and Metal Pad Conditioning Process

*B.-K. Kang¹, Y.-J. Kang¹, K.C. Kim¹, J.-G. Park¹
J.-H. Lee², J.-S. Ahn²;*

¹*Hanyang University, Ansan, Korea;*

²*Ehwa Diamond Ind. Co., Ltd., Osan, Korea*

Accelerating Development Timeframes Through Effective Use of CMP Outsourcing

R. Carroll¹, L. Rhoades²;

¹*Polar Semiconductor Inc., USA;*

²*Entrepix Inc., Tempe, AZ, USA*

Point of Use Quality Control of CMP Slurries

F. Hinze, J. Altmann; Aello, Dresden, Germany

Optimizations of Post Polish Procedure for Defect Density Reduction

H. Lauber, S. Muenzberger; Infineon Technologies, Dresden, Germany

Fabrication of Surface Acoustic Wave Structures with buried Copper IDTs using the Copper Damascene Process

*S. Menzel¹, D. Reitz¹, U. Künzelmann², M. Albert²,
J.-W. Bartha²;*

¹*Leibniz-Institute for Solid State and Materials Research (IFW), Dresden;*

²*Dresden University of Technology, Dresden, Germany*

Material & Design Considerations for Zero Defect CMP Pads

R. Carpio¹, F. Tolic¹, S. Hymes², R. Bajaj²;

¹*ATDF, Austin, TX, USA;*

²*SemiQuest Inc., San Jose, CA, USA*

Saturday, October 27, 2007

Social Day
“World Heritage Discovery Tour”

Experience the Dresden Elbe valley from the land, from the air and from the water. During a combined walking and coach tour, we would like to introduce a cultural landscape which has evolved over the course of 800 years. Learn more about the famous sights of the city, such as the Zwinger, Semper Opera House and Frauenkirche. The journey continues past broad green meadows and below the so-called Elbe palaces to the oldest suspension railway in the world.

From the Loschwitz Heights, you can enjoy a magnificent view over the whole Elbe valley. The next stopping point is no less fascinating: Pillnitz Palace and Park. During a tour of the complex, you will become acquainted with the history, architecture and landscape gardening of this unique integral work of art. Alongside the dendrological treasures of the park, we will also show you around one of its pavilions, the Catholic palace chapel and the historical palace kitchens. During the return journey to Dresden aboard a paddle-steamer, you can relax and absorb once more the harmony of urban and natural landscapes.

09:00 h Tourist Guide starts the walking tour at the Theaterplatz/Reiterdenkmal near the Semper Opera House

16:45 h End of tour at the Elbeterassen

Please make your registration in good time. Bookings for excursions will be made on a “first come - first served” basis upon receipt of registration and payment.

The total amount shall be paid in advance or at the registration desk and has to be made in EUR.

CONFERENCE INFORMATION

CONFERENCE HOURS

Thursday, October 25, 2007	09:00 h to 18:40 h
Friday, October 26, 2007	08:30 h to 18:10 h

REGISTRATION HOURS

Wednesday, October 24, 2007	17:00 h to 19:00 h
Thursday, October 25, 2007	07.30 h to 09:30 h

EXHIBITION

The two-day tabletop exhibition is an integral part of the ICPT 2007 conference and takes place at an exhibition area close to the conference lecture room which can be visited during all coffee and lunch breaks.

Exhibition space of 4 m² or 6 m² (40 sqft or 60 sqft) with table, two chairs and poster board are available. Registration for the exhibition includes two full access badges, two copies of the proceedings and a company name listing in all promotional materials.

For further information on the exhibition please contact
Dr. Ronald Schnabel
Stresemannallee 15
D-60596 Frankfurt am Main, Germany
Phone: ++49-69-6308-330, Fax:++49-69-6308-9828
E-Mail: gmm@vde.com

INFORMATION FOR AUTHORS

MANUSCRIPTS AND PROCEEDINGS

Manuscripts should be send to conference-papers@vde.com by **August 24, 2007**. Since the manuscripts will be directly reproduced in the proceedings please send a pdf-file by e-mail. The manuscripts are limited to 6 pages (figures included). When writing respectively shaping your manuscript, please observe the "Instructions for paper preparation", which you will find at <http://www.ICPT2007.com>

The conference proceedings and CD-ROM will be published by the VDE/VDI Society Microelectronics, Micro- and Precision Engineering and will be delivered to the conference participants at the registration desk.

Please note that late submissions may not be considered in the conference proceedings.

GENERAL INFORMATION

ICPT 2007 SECRETARIAT

For detailed Information please contact:

VDE/VDI-Society Microelectronics, Micro- and Precision
Engineering (GMM)
Dr. Ronald Schnabel
Stresemannallee 15
D-60596 Frankfurt am Main, Germany
Phone: ++49 69 / 6308-330
Fax: ++49 69 / 6308-9828
E-Mail: gmm@vde.com
During the conference:
Phone: ++49 171 4695 118

CONFERENCE FEES

	until Sept. 25,2007	after Sept. 25,2007
Non-Members	€ 390,00	€ 440,00
VDE, VDI-Members*	€ 350,00	€ 400,00
Lecturer	€ 350,00	€ 400,00
Exhibitor (max. 2 people)	€ 0,00	€ 0,00
Non-Member-Students**	€ 40,00	€ 70,00
Student Members**	€ 20,00	€ 50,00
Extra proceedings	€ 60,00	€ 60,00
Discovery tour 27.10.2007	€ 70,00	€ 70,00

* Participants applying for the membership fee must include a copy of their membership card to the registration form.

** A photocopy of the student card must be included.

The conference fee includes admission to all sessions as well as to the daily coffee-breaks and lunches, one copy of the proceedings including a CD-ROM, conference dinner on Thursday.

CONFERENCE REGISTRATION

To register for ICPT 2007 please fill in the registration form attached to this program and return to VDE Conference Services, Stresemannallee 15, 60596 Frankfurt, Germany. To enjoy the "early-bird-discount", VDE Conference Services must receive the form before September 25th, 2007. Full payment or credit card information must accompany all registrations in order to be accepted. Completed forms may be sent by fax (+49 69 96 31 5213) surface mail or e-mail (vde-conferences@vde.com). A confirmation of the registration will be sent upon receipt of full payment.

ONLINE REGISTRATION

Registrations for the conference may be done online on the conference homepage www.icpt2007.com

PAYMENT TO THE VDE/VDI SOCIETY

Payment for registration, including bank charges and processing fees, must be made in Euro.

The conference fee has to be fully paid in advance. Confirmation of registration will be sent after full payment has been received at the VDE-Conference Services.

The following methods of payment are accepted:

- Cheque in EURO (€) payable to VDE and sent together with the registration form by mail.
- By credit card authorisation as per registration form. The 16 digit card number, expiry date, security No. (last 3 digits on rear side of credit card) and holder's name must be indicated on the registration form. Signature of the card holder is mandatory.
- Cash payment on-site in EURO (€)

CANCELLATION

In case of cancellation, provided that written notice is received at the VDE-Conference Services before Sept. 25, 2007, the registration fee will be fully refunded less a handling fee of EURO 60,00. After Sept. 25, 2007 no refund will be made. Proceedings and CD-ROM will then be sent to the registrant after the conference.

PROCEEDINGS

All papers accepted for presentation at the conference will be published with the proceedings and a CD-ROM. The proceedings will be handed on-site to all delegates attending the event.

Additional proceedings and CD-ROM are on sale during the conference (upon availability) at EURO 60,00

CONFERENCE VENUE

Hilton Dresden
An der Frauenkirche 5
D-01069 Dresden, Germany
Phone: +49 351/86420
Fax: +49 351/8642-725

Hilton Dresden, located in the heart of the old town, next to the Frauenkirche, is situated on Bruehl's Terrace. The Semper Opera House and the world-renowned "Zwinger" are within walking distance. The piers of the world's largest and oldest paddle steamer fleet are next to the hotel.

HOTEL RESERVATION

A block of rooms has been reserved for ICPT 2007 participants

Hilton Hotel Dresden

The hotel room rate (special rate, including breakfast) is

165,00 EURO (single room classic),
190,00 EURO (double room classic)

190,00 EURO (single room deluxe),
215,00 EURO (double room deluxe)

220,00 EURO (single room executive),
245,00 EURO (double room executive)

per night. Accommodation is not included in the conference fee. Please contact the Hilton Hotel, for reservation.

Hilton Dresden
An der Frauenkirche 5
D-01069 Dresden, Germany
Phone: +49 351 / 8642-0
Fax: +49 351 / 8642-725
E-Mail: info.dresden@hilton.com
<http://www.hilton.com/>

You should reserve your room by September 12th, 2007 or our block of rooms at the Hilton Hotel may be released by the hotel for general sale. Please use the following code for booking: "ICPT 2007"

Ramada Hotel Dresden

The hotel room rate (special rate, including breakfast) is

93,00 EURO (single room comfort),
107,00 EURO (double room comfort)

per night. Accommodation is not included in the conference fee. Please contact the Ramada Hotel for reservation.

Ramada Hotel Dresden
Wilhelm-Franke-Straße 90
D-01219 Dresden, Germany
Phone: +49 351 / 4782-0
Fax: +49 351 / 4782-550
[http:// www.ramada-dresden.de](http://www.ramada-dresden.de)

You should reserve your room by August 24th, 2007 or our block of rooms at the Ramada Hotel may be released by the hotel for general sale. Please use the following code for booking: "ICPT 2007"

All payments related to accommodation have to be made directly on departure in the hotel.

BUSSHUTTLE

There will be a busshuttle from the Ramada Hotel to the Hilton Hotel on both conference days. The bus will depart half an hour before the beginning of the conference on Oktober 25 and 26, 2007.

INSURANCE

The organisers may not be held responsible for any injury to participants or damage, theft and loss of personal belongings.

PASSPORT AND VISA REQUIREMENTS

Foreign visitors entering Germany have to present a valid Identity Card or Passport. Delegates who need a visa should contact the German consular offices or embassies in their home countries. Please note that neither the VDE-Conference Services nor the VDE/VDI-Society Microelectronics, Micro- and Precision Engineering (GMM) or the supporting bodies are able to extend any "Invitation" for application of visa.

TRANSPORT

By Air

Dresden Airport

Distance from hotel: 10 km, Drive time: 20 min.

Directions: Follow signs to city centre. After passing the Elbe Bridge, turn right onto Terrassenufer. Follow Hilton signs.

Getting to and from the airport

Bus Service, typical minimum charge is EURO 8,00

Limousine, typical minimum charge is EURO 70,00

Taxi, typical minimum is EURO 25,00

By train

from Frankfurt in 5 hours

from Berlin in 3 hours

LIST OF EXHIBITORS

3M Company, St. Paul, USA
Abrasive Technology, Ohio, USA
AGC Electronic Materials, Hillsboro, USA
Araca, Inc., Tucson, US
ATDF, Inc., Austin, USA
Cabot Microelectronics, Aurora, USA
ECO Physics AG, Dürnten, Suisse
Ehwa Diamond Ind. Co. Ltd., Osan, Korea
Entegris GmbH, Dresden, Germany
Euris GmbH, Tübingen, Germany
G&P Technology, Inc., Busan, Korea
JSR Micro N.V., Leuven, Belgium
Kemesys, Peynier, France
Mitsubishi Materials Corp., Tokyo, Japan
Morgan Advanced Ceramics, Allantown, PA, USA
Pall GmbH, Bad Kreuznach, Germany
Qimonda AG, Dresden, Germany
Rohm und Haas Electronic Materials, Dresden, Germany
Samsung Cheil Industries Inc., Uiwang-Si, Geyoinggi-Do, Korea
Shinan Diamond Industrial Co., Ltd., Incheon, Korea
SPS-Europe B.V., Putten, The Netherlands
Struers GmbH/Logitech Ltd, Willich, Germany
Umicore, Olen, Belgium

Notes

The IPCT 2007 Organizing Committee would like to express its sincere appreciation to the following companies for their support:

